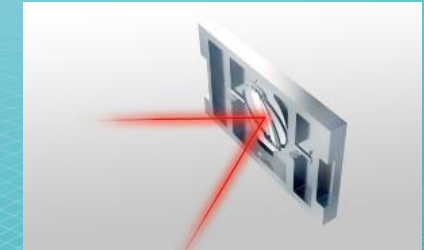


Fraunhofer-Institut für Photonische
Mikrosysteme IPMS



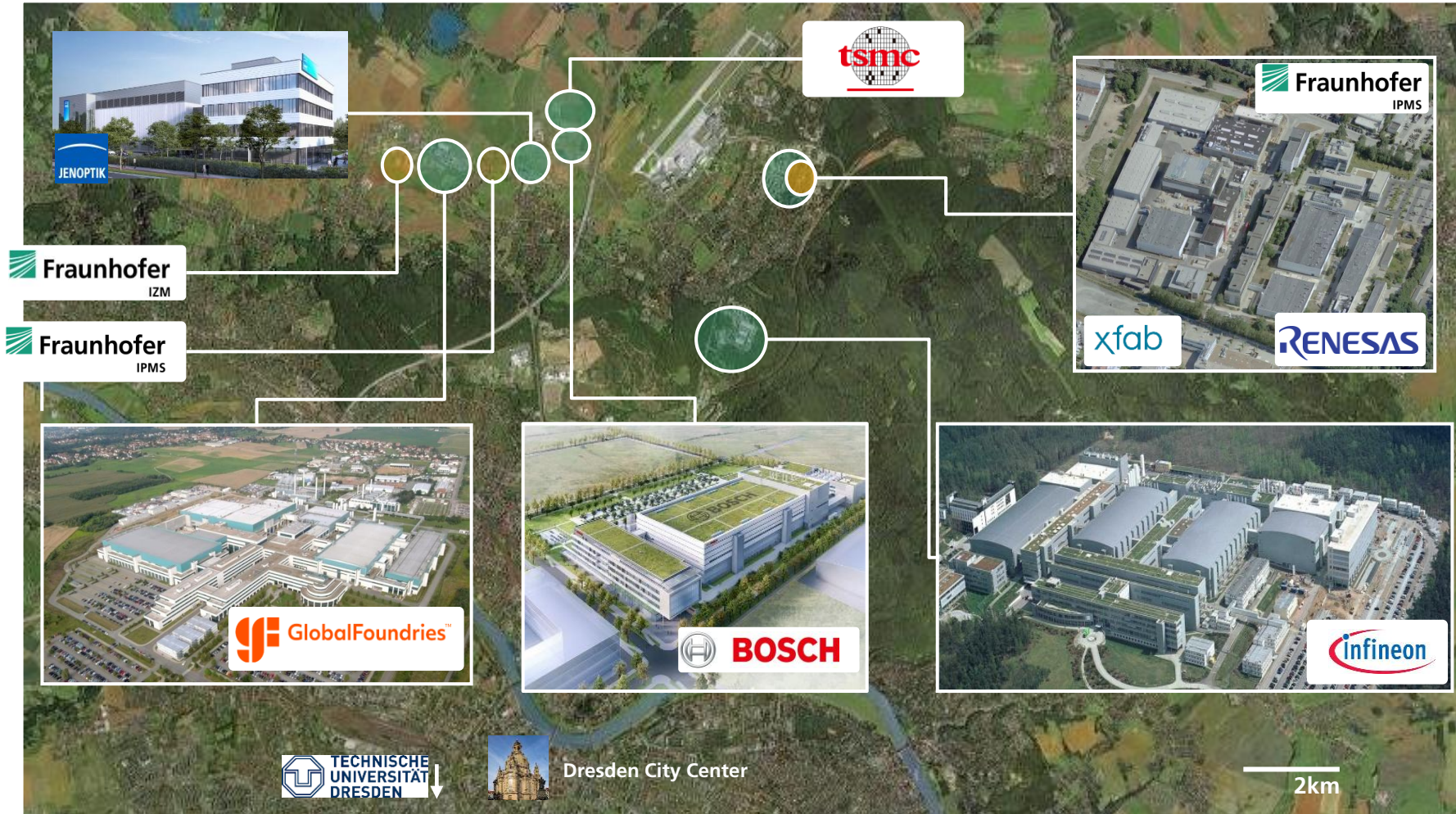
„O/LED Microdisplays for Near-to-eye wearables and Embedded Quantum-based Sensing“

U. Vogel & colleagues

Fraunhofer Institute for Photonic Microsystems IPMS, Dresden, Germany

Silicon Saxony -

■ The Heart of European Microelectronics Beats in Dresden



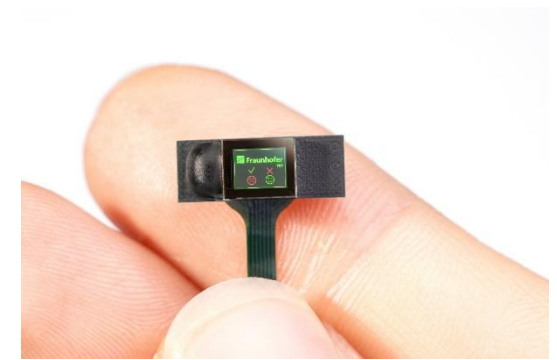
Silicon Saxony

Every third chip produced in Europe comes from Saxony.

Microdisplays (general)

■ Definition

- Physically very small (<1.3"), yet
 - High information content (TV quality)
 - $\geq 1000\text{ppi}$, i.e. pixel pitch $\leq 25 \times 25 \mu\text{m}$,
 - typically $2.5 \mu\text{m}$ dot pitch (i.e., 2000..3000..5000ppi)
 - Active matrix substrate (mostly CMOS)
 - Low power consumption
 - Enlarged image viewed through magnifying optics



■ Applications

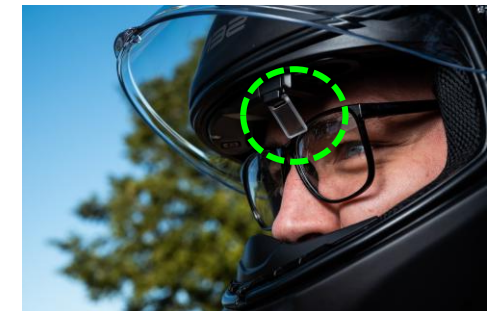
■ Projection

- Rear projection
- Front projection
- Micro projection



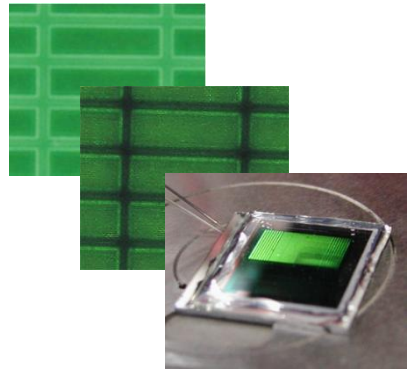
■ Near-to-Eye (NTE)

- Electronic Viewfinder (EVF)
- Hand-held
- Head/helmet Mounted
 - Professional, Consumer
 - Augmented-, Virtual-, Mixed-Reality (AR, VR, MR)

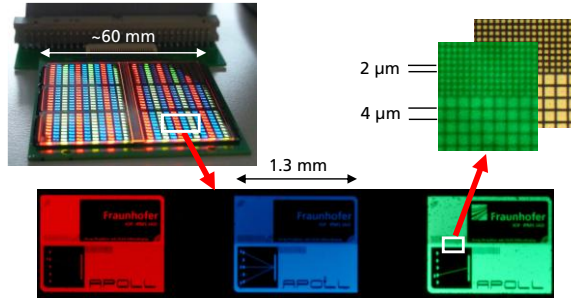


OLED microdisplay history (Roadmap based on customer requests) (1)

Microdisplays



QVGA
0.16", 6300dpi
9x11 patched array
Array colour



WUXGA
1", 4618dpi
Full color



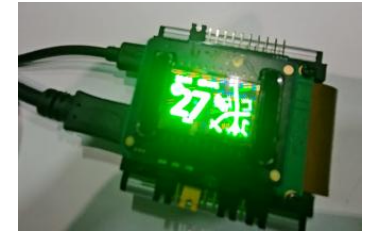
d: QVGA
0.19", 4233dpi
Ultra-low power
Bi-color



SXGA
0.62", 7938dpi
Full color, high-voltage



WUXGA
1", 2309dpi
high-current (microLED)



QVGA
0.24", 5000ppi
Full color



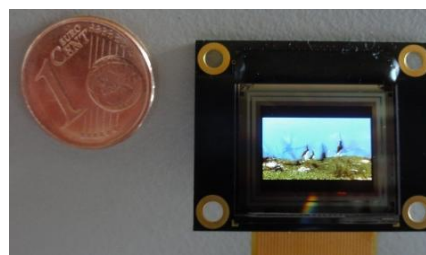
VGA
0.4", 6300ppi
Full color



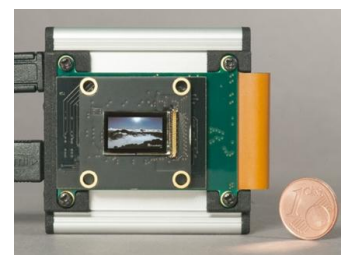
XGA, Rev 1
0.6", 6300dpi
Full color



XGA, Rev 2
0.6", 6300dpi
Full color



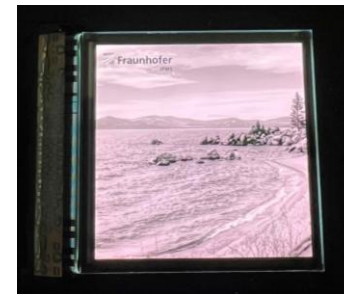
720p
0.64", 4618dpi
Full color



1080p
0.19", 10160dpi
Mono color



2k x 2k
1.1", 5462dpi
High-voltage, LVDS



2007

2010

2016

2018

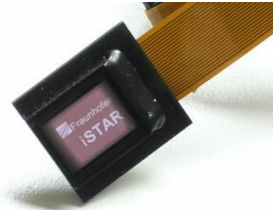
2025

OLED microdisplay history (Roadmap based on customer requests) (2)

■ Bi-directional, embedded sensing, semi-transparent, scanner



0.15" d: 40x32, mono
s: 20x16, VIS

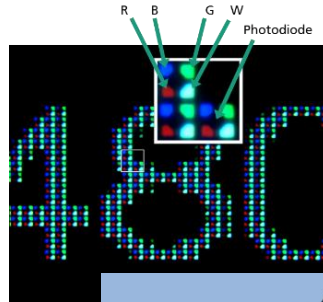


d: VGA, full color
s: 128x96, mono VIS/NIR
0.5", 3200dpi



Embedded sensing (non-imaging reflection, flow, color)

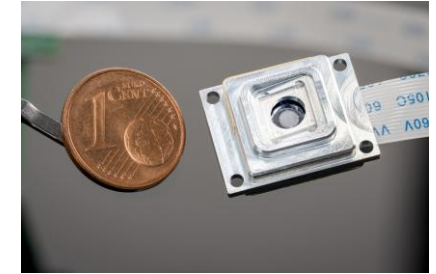
0.6", d: SVGA, 3175dpi, full color;
s: SVGA, 1588dpi, mono



Embedded sensing (non-imaging chromophore excitation and readout)



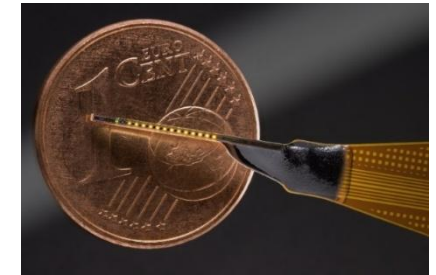
MEMS micro-scanning mirror



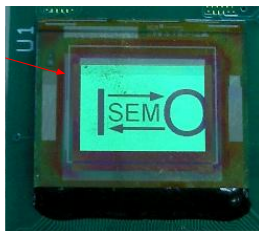
0.6" SVGA OPD image sensor, NIR



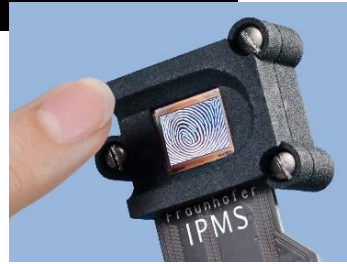
Active micro-optical probe



d: QVGA, mono
s: 160x120, mono VIS
0.6", 700dpi

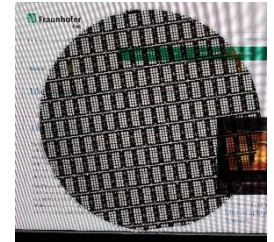
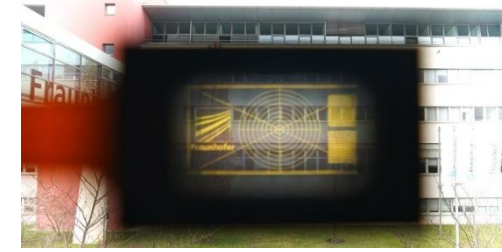
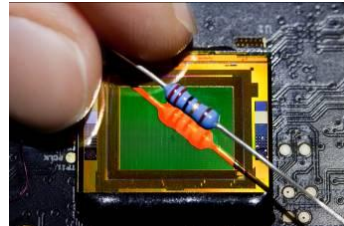
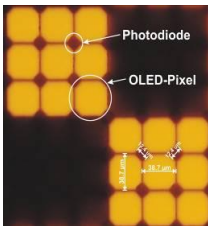


d: QVGA, area color + NIR
s: 160x120, mono VIS
0.6", 700dpi



1" WUXGA, 4618dpi, curved

0.7" semi-transparent patched array, 7257dpi, mono

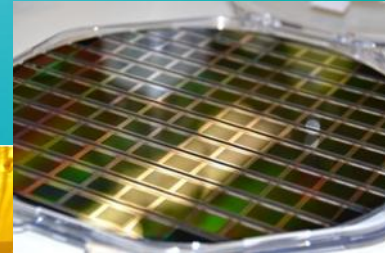
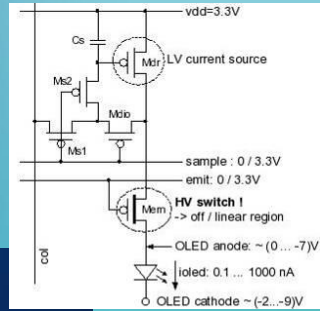


2007

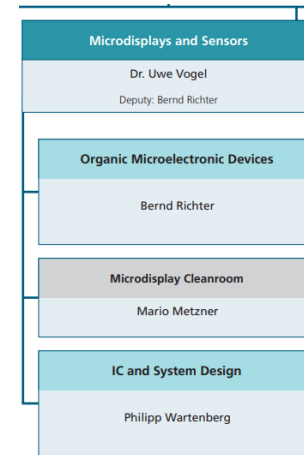
2025

Core competences

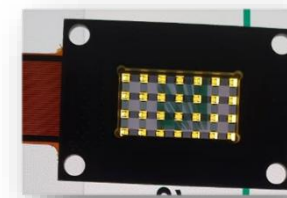
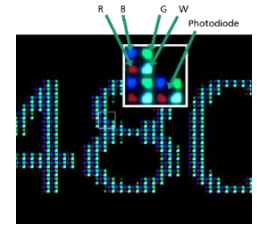
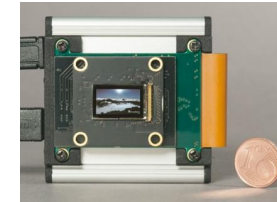
IC design (backplane, 8/12" foundries)



Organizational structure



Example outcomes

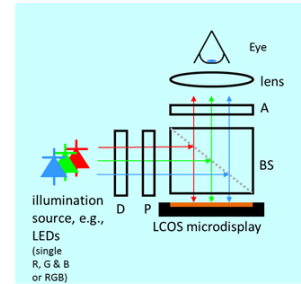
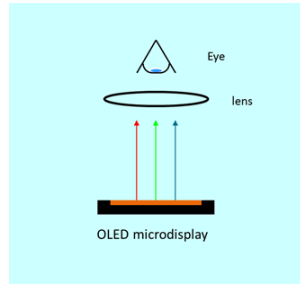


Microdisplay technology

Light source = image modulator

Light source ≠ image modulator

-> separate devices



Microdisplay technology

Emissive (non-transparent)

transmissive

scanning

reflective

OLED-on-Silicon

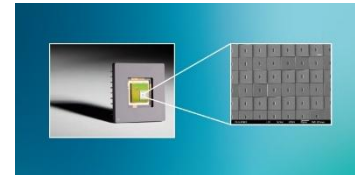
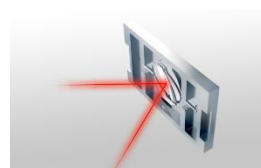
microLED III/V-on-Si

O/LED vs. LCD

MEMS scanner

MEMS SLM (DMD)

LCOS



Heterogeneous
<i>Monolithic</i>
Sole substrate
OLED-on-CMOS

Heterogeneous
<i>Hybrid</i>
Multiple substrates
μLED + CMOS

Professional Use Case 1 - Full Video Display

- Application Scenario
 - True augmented-reality, VR
 - Real-time overlay of sensor / image data
- Typ. Requirement
 - High-resolution (720p, FHD, 4k...)
 - High-framerate (60Hz...120Hz)
 - Mono, multi, full-color
 - Extreme low- to extreme high-brightness
 - Typ. power >100mW
- System Consequence
 - Complex optics/electronics



Low Brightness

U.S. Army @ Youtube



Theon



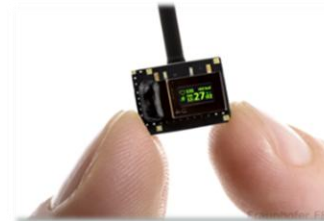
High Brightness



SA Photonics

Use Case 2 - Information Display

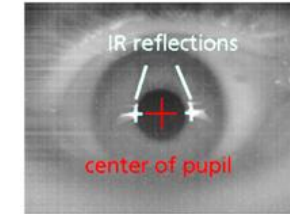
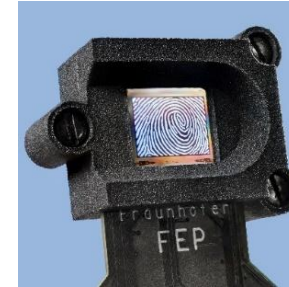
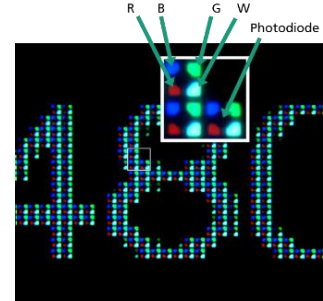
- Application Scenario
 - Assisted-reality/'light AR': Visualization of data w/o overlay or augmentation
 - Mobile navigation, status information, logistics...
- Typ. Requirement
 - Small, light-weight, no heat, long battery life
 - Low- to mid-resolution (QVGA...VGA)
 - Low-framerate (0 ... 60Hz)
 - Extreme low to extreme high brightness
 - Typ. power 1mW
 - Simple system



OLED-on-Silicon/CMOS: Unique Features, devices and applications

■ Bi-directional

- Display and image sensor in single chip
- AR, VR, Eye-tracking; Optical fingerprint, Surface inspection, medical



■ Ultra-low power

- 1mW range: Wearables, electronic viewfinder, assisted-reality

■ Highest pixel density

- >10kdpi, deep sub-micron CMOS



■ Semi-transparent

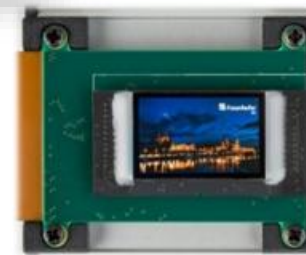
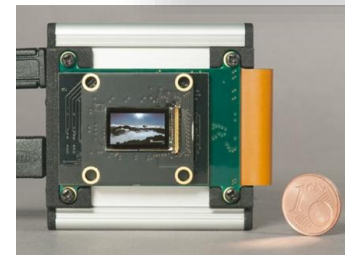
- Combiner-less see-through AR

■ Large-area

- very high-definition (>FHD)
- VR, AR, micro-projection

■ High-brightness

- High-current (microLED), high-voltage (stacked OLED)

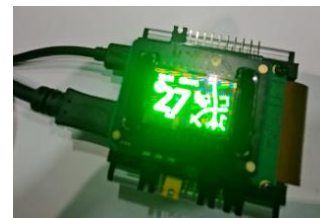


■ NIR imager

- Organic photodiodes (OPD) on silicon CMOS

■ embedded sensors

- Gas or liquid process monitoring, e.g., O₂, pH

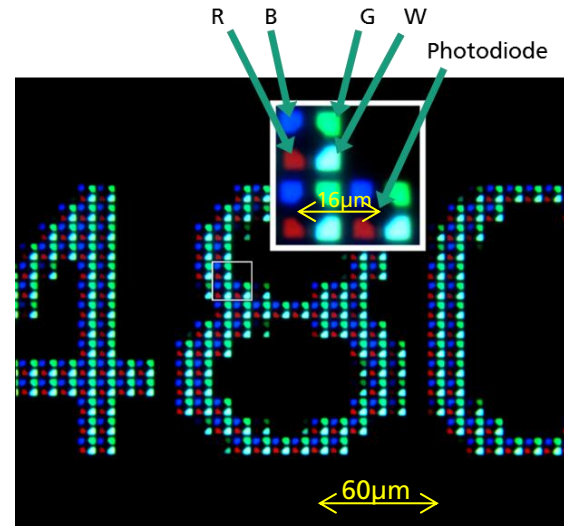
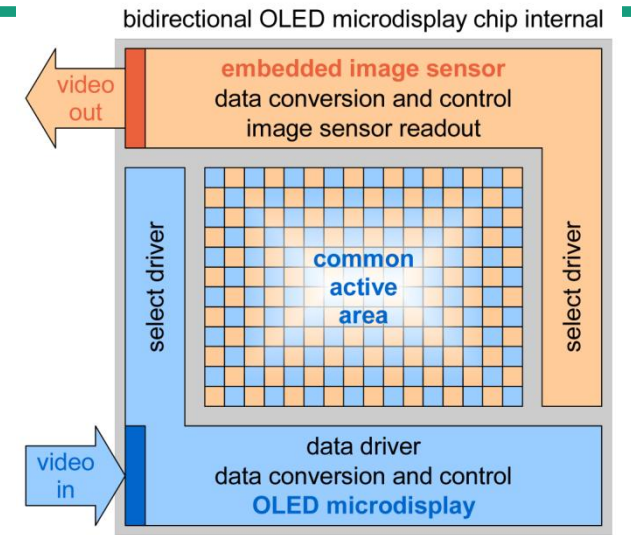
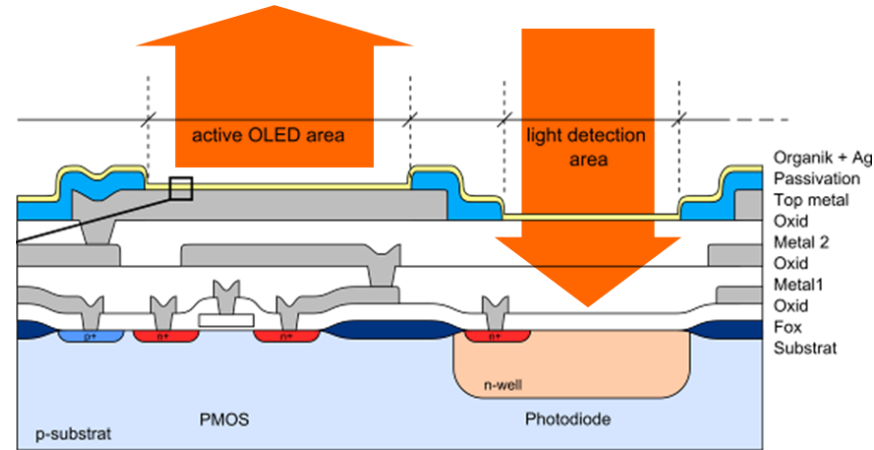


■ Pilotfabrication- and Field-proven

OLED-on-Silicon + embedded photodetectors/imager

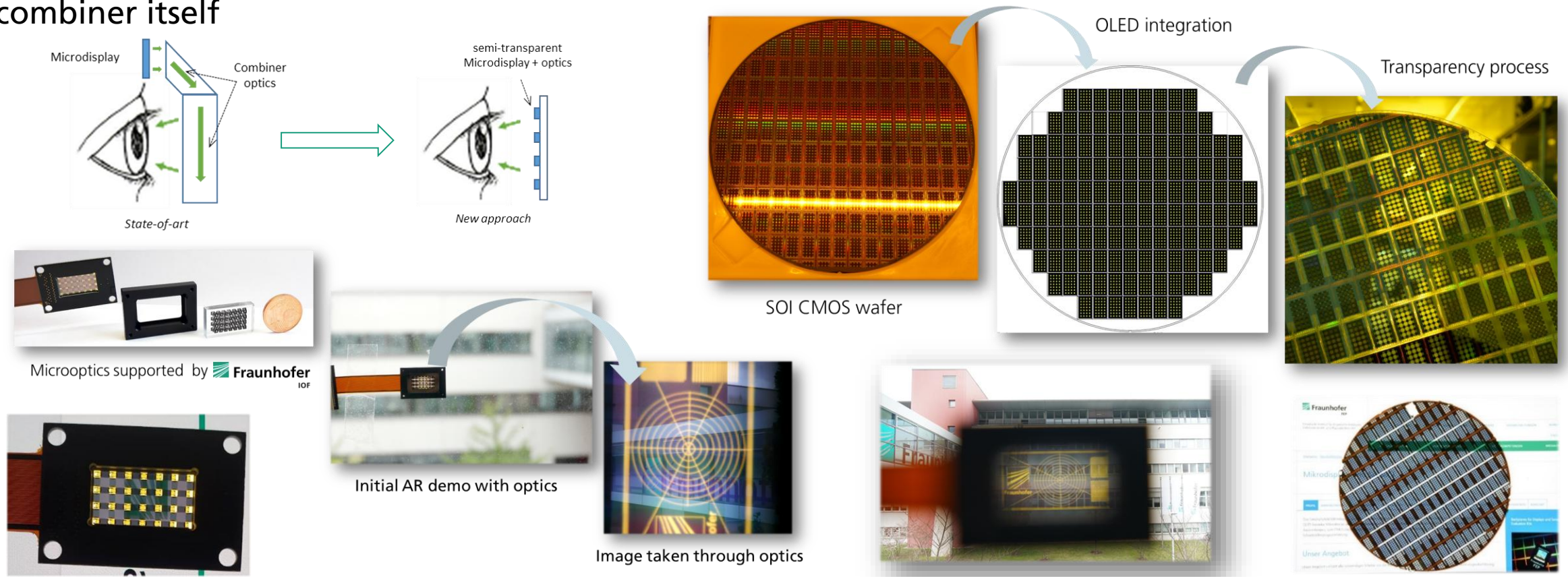
Highly-efficient high-res light source and imager on single chip

- Bi-directional OLED microdisplay
 - Patterened illumination
 - Excitation/stimulation
- Spectral sensitivity photodetectors
 - CMOS: 400..900nm
 - OPD: 300..>1000nm



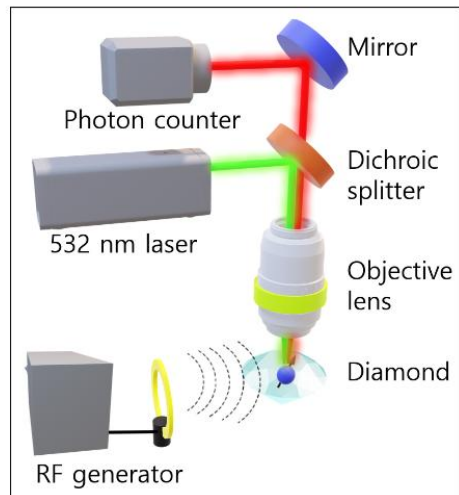
Semi-transparent OLED microdisplays for EPE-less optical see-through

- Waveguides typically require high-luminance light sources (due to low optical efficiency)
 - -> light engine high power consumption required -> too much for wearables (<1Wh)!
- Get rid of separate exit pupil expander (EPE), by making microdisplay backplane semi-transparent to become combiner itself

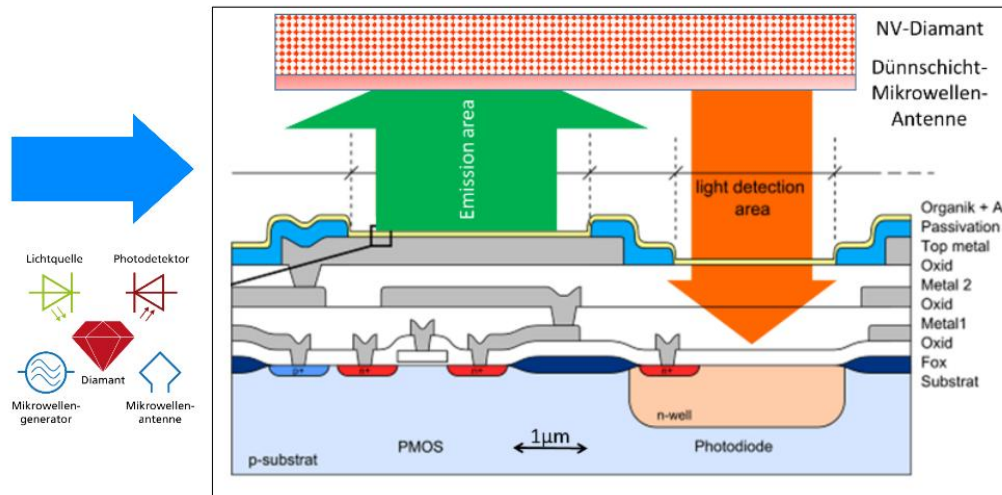


OptoQuant

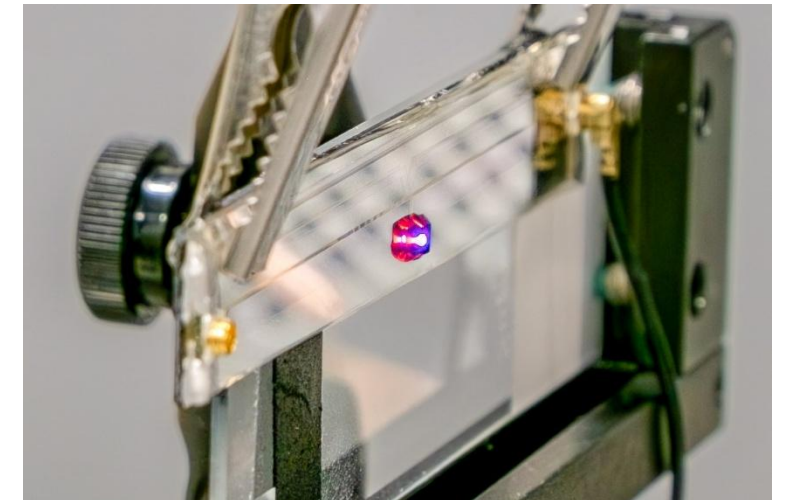
- *CMOS-integrated, micro-optoelectronic room-temperature quantum-sensing for high-sensitivity magnetic field imaging*
 - Magnetic textures or electrical current imaging based on optical or scanning magnetometry with NV centers
 - CMOS-integrated NV sensor with built-in optical excitation, optical detection, and microwave generation and delivery
 - prototype with multiple channels of integrated sensor, to allow for imaging



Traditional NV sensor (meter scale)



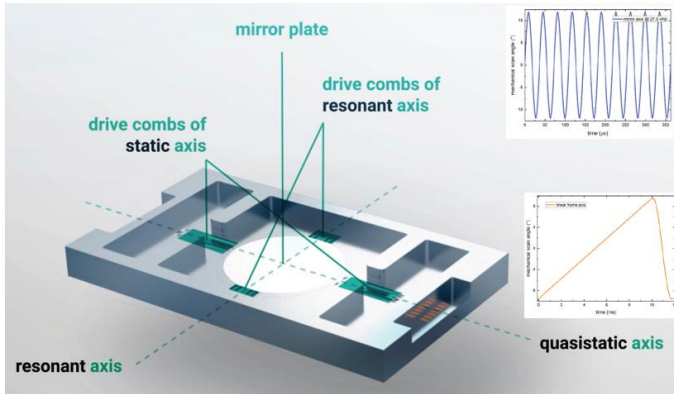
CMOS-integrated NV sensor (μm scale)



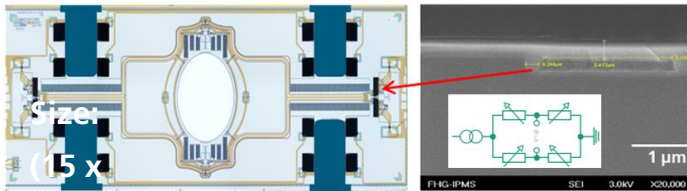
MEMS Scanning Mirrors

Electro-Static (monolithic)

2D-Raster MEMS-Scanner Technology:
USP: Monolithic integrated (PZR) Position Sensing



Setup of a Linscan microscanner with second resonant axis



2D Resolin-Scanner QS-MSA: 9°; RS-MSA: 17° SEM-figure of PZR sensor

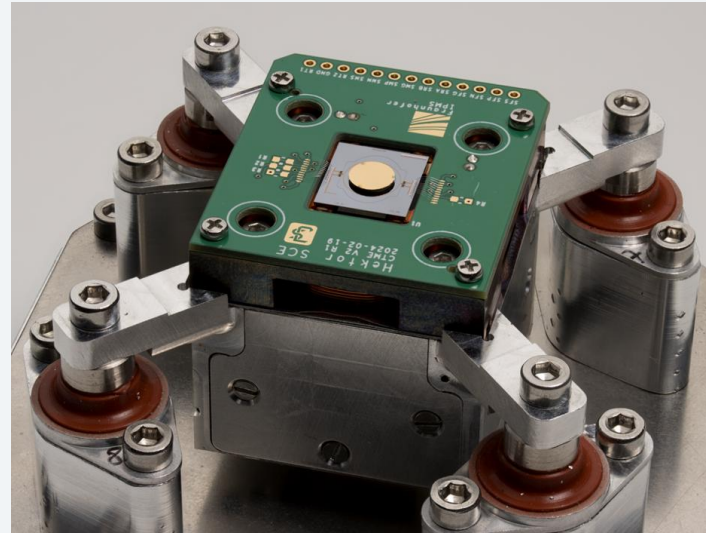
Size: (15 x 20 x 9.5) mm



Electrostatic MEMS Vectorscanner:

- 1kHz,
- 2.4mm aperture

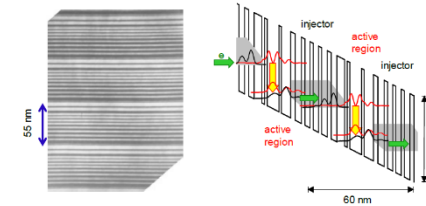
Electro-Magnetic (hybrid) 2D-Vectorscanner



MEMS Vector Scanmodule with vibration isolation for space LIDAR

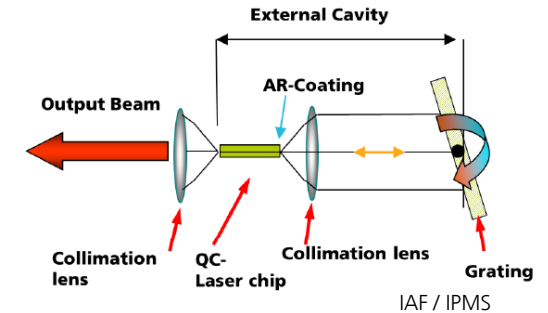
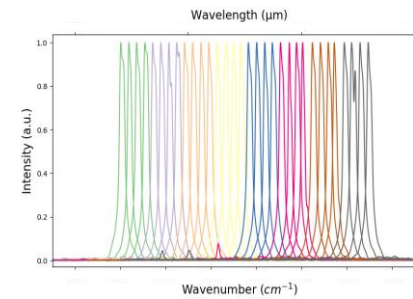
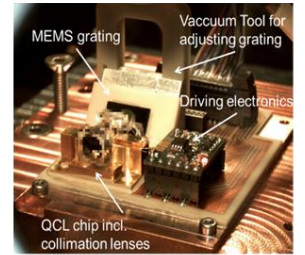
Parameter	Value
Large 2D-QS angle	± 13° @ QS mech.
Large aperture	D = (5 ... 10) mm
Eigen-frequency	170...270 Hz or higher
actuating speed	(100 ... 1000) %s
driving current	ca. 20 mA ¹⁴

MIR tunable QCL – Quantum Cascade Laser



Left: SEM photo of epitaxial layers. Right: Bandgap diagram of QCL

Integrated in μ EC-QCL (IAF)



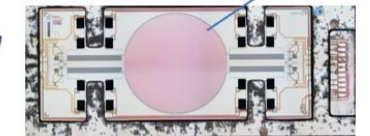
- ❖ MOEMS scanning grating devices for broad band wavelength tuning of miniaturized EC-QCL
- ❖ Fabrication of resonant and quasi-static MOEMS devices with integrated diffraction gratings covering $\lambda = 3...10 \mu\text{m}$ MIR range

Resonant MOEMS grating

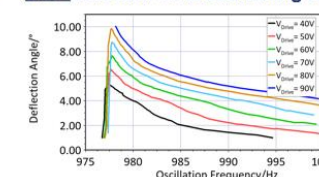


Ø5 mm IR diffraction grating

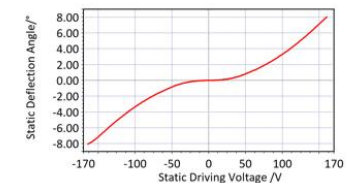
Quasi static MOEMS grating



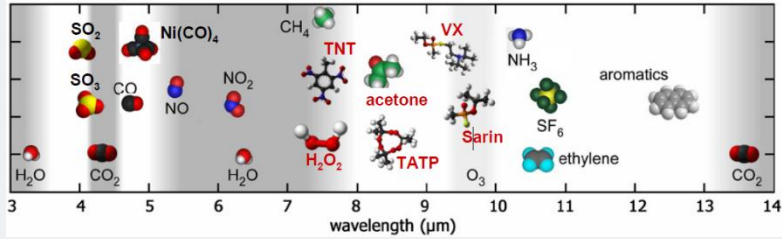
- scanning with 150 Hz, 500 Hz or 1 KHz rate \rightarrow 0.5 ms for one full spectral scan
- ±10° deflection for broad tuning range



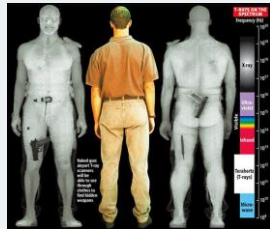
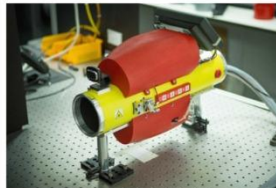
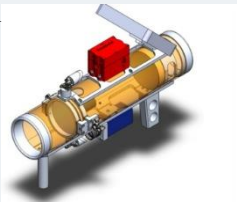
- tuning to single wavelength or arbitrary spectral scanning at 0...50 Hz scan rate ±8° deflection



MIR tunable QCL - Quantum Cascade Laser



Example molecules with mid-IR “fingerprint” signatures.



QCL-based airport security scanner



ABC detection tank Fuchs (D)

- Remote Sensing
- Trace gases detection
- Non-contact explosives detection
- Through-solidus-sensing and THz Imaging
- infrared countermeasures (IRCM)
- beacons (combat identification)

Applications: MEMS *Vector* Scanners

Compact LiDAR sensors for Space:

- Rendezvous- and Docking Sensors
- Service robotics / maintenance of satellites
- removing of space debris
- Rover Navigation of moon / planet missions

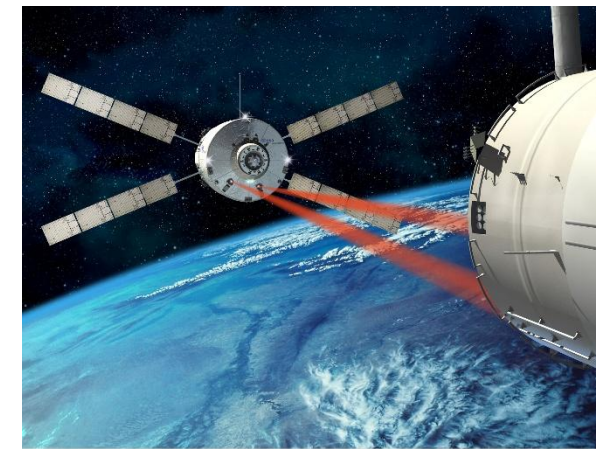
Aviation:

- Obstacle detection e.g. for fast low-altitude flight of helicopters

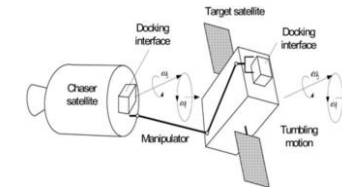
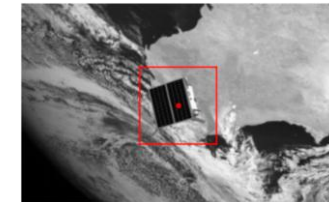
Security:

- Monitoring of critical infrastructure
- 3D surveying with drones

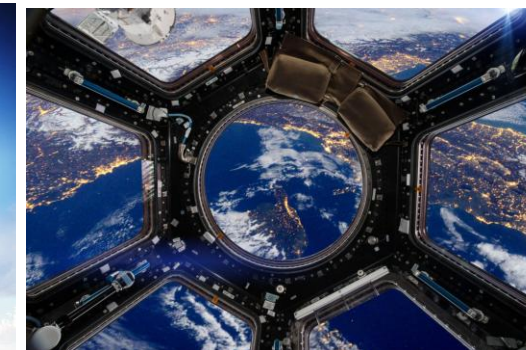
Free Space optical communication (FSO)



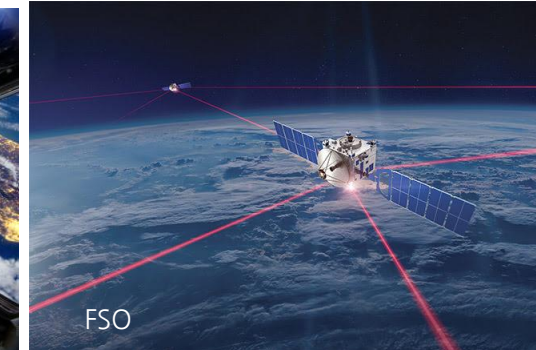
© ESA/D. Ducros - 2007



S15



3/11/2026



FSO

Outlook: O/LED-on-Silicon/microdisplays features and applications

high-brightness

- see-through near-to-eye @ sun light condition
- embedded projection
- **Medical and biological applications**, e.g., optogenetic brain/nerve interfaces, emergency medicine, microbiological synthesis

high-resolution

- Pixel densities >10kppi
 - Light-field and holographic displays
 - smaller chip size, lower cost

(embedded) sensing

- Single-chip image converter
- Quantum sensors (very-low magnetic fields)

(embedded) computing/connectivity

- Edge Vision + Edge AI
- Deep sub-micron CMOS process backplanes on 300mm (LVDS, MIPI, Bluetooth)

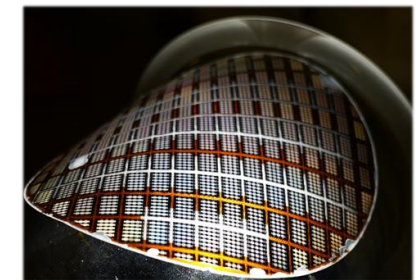
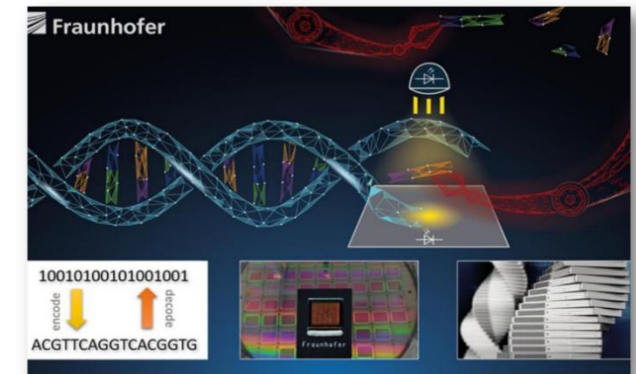
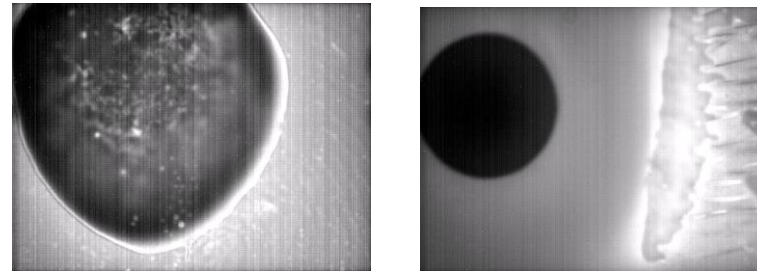
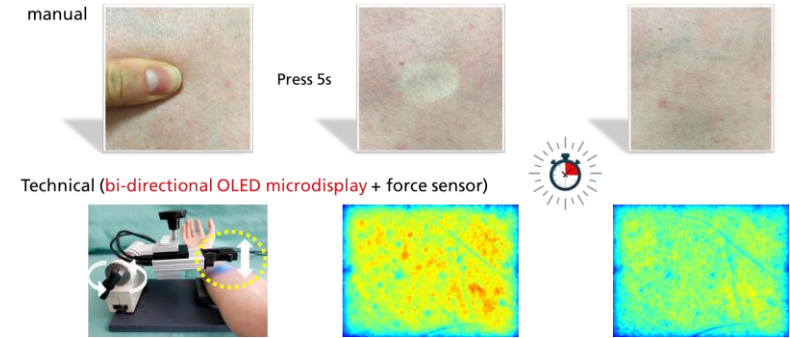
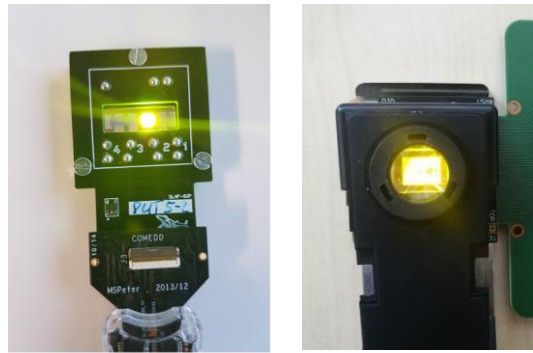
extended spectral emission and detection range

- UV, IR; α , β , γ ; μ LED

New form factors, e.g., transparent & curved microelectronics

- e.g., smart contact lens display

Manufacturing processes: yield, production costs



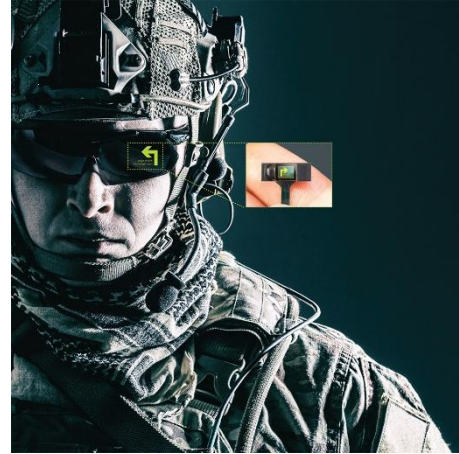
In-person Conference Announcement

“***Augmented Vision: Displays for Defense***”

March 16./17. 2026 (Mo/Tue)

Hosted by LusoVu in Lisbon/Portugal

- Venue: Jupiter Hotel Lisbon
- Schedule:
 - 1st day: Mon, March 16
 - Morning:
 - [Virtual Worlds Association \(VWA\) Workshop on Future “XR chips & components pilot-line”](#)
 - LusoSpace company tour (reservation required)
 - Afternoon (1pm+): sessions
 - evening event at rooftop Jupiter Hotel (sponsored by LusoVu)
 - 2nd day: Tue, March 17, 9am..3pm: sessions
- **Speakers:**
 - Portuguese Army (PT), Bundeswehr (DE), Portuguese Navy (PT), ENGO (FR), L3Harris (US), Polar Light Technologies (SE), FlexEnable (UK), Dispelix (FI), LusoVu (PT), MicroOled (FR), Schmidt & Bender (DE), CEA-LETI (FR), Fraunhofer (DE),...



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Already Registered?

SID
MID-EUROPE CHAPTER

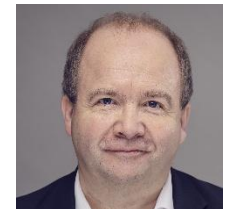
SID - Mid Europe Conference 2026

March 16, 2026 – March 17, 2026
Jupiter Lisboa Hotel
Lisbon, Portugal

SUBMIT ABSTRACT



Ines Cadilha
LusoVU Lda
Executive Chair



Dr. Uwe Vogel
Fraunhofer Institute for Photonic
Microsystems IPMS
General Chair

Thanks for your attention!

■ Offer

- R&D on Customer-/applications-specific components and devices,
- Manufacturing technology, pilot-fabrication
- Private and publicly funded collaborative projects
- Technology transfer/licensing

■ Seek

- Application specifications
- Devices/technology evaluation (pilot studies)
- System integration (optics, electronics, sensors, communication,...)
- Applications (viewfinder, image converter, AR/VR/MR, sensing, ...), end user

■ Dr. Uwe Vogel

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- Fraunhofer Institute for Photonic Microsystems IPMS
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 - phone: +49-151-12174078
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- Chair „Society for Information Display“ Mid-Europe Chapter (<https://www.sid.org/Chapters/Europe/Mid-Europe#6501368-home>)

- Chair GMM FA4.2 „Photonics & Microoptics“

- Chair DKE UK742.7 „Electronic Displays“ (DENC IEC TC110 mirror „Electronic Displays“)

